Silicon PNP Epitaxial

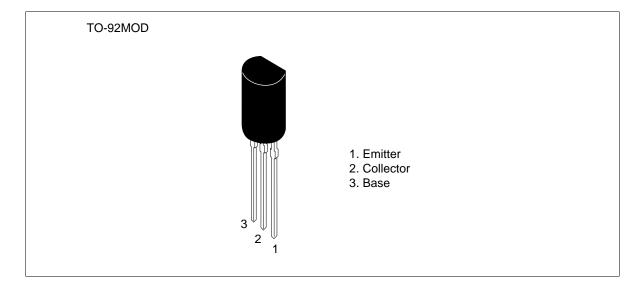
# **HITACHI**

ADE-208-1030 (Z) 1st. Edition Mar. 2001

### Application

- Low frequency power amplifier
- Complementary pair with 2SD787 and 2SD788

#### Outline





## **Absolute Maximum Ratings** (Ta = 25°C)

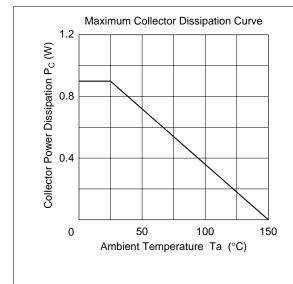
Item	Symbol	2SB738	2SB739	Unit
Collector to base voltage	$V_{\text{CBO}}$	-20	-20	V
Collector to emitter voltage	V <sub>CEO</sub>	<b>–</b> 16	-20	V
Emitter to base voltage	$V_{EBO}$	<b>–</b> 6	-6	V
Collector current	I <sub>c</sub>	-2	-2	Α
Collector power dissipation	P <sub>c</sub>	0.9	0.9	W
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

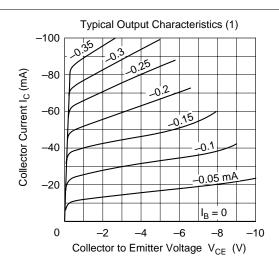
### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

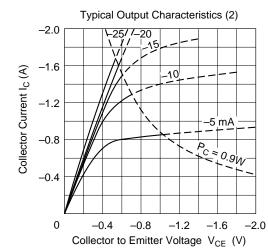
		2SB738		2SB739					
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-20	_	_	-20	_	_	V	$I_{c} = -10 \mu\text{A},  I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-16	_	_	-20	_	_	V	$I_{C} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	_	_	-6	_	_	V	$I_E = -10  \mu A, I_C = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-2	_	_	-2	μΑ	$V_{CB} = -16 \text{ V}, I_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_	_	-0.2	_	_	-0.2	μΑ	$V_{EB} = -6 \text{ V}, I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	100	_	320	100	_	320		$V_{CE} = -2 \text{ V}, I_{C} = -0.1 \text{ A}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-0.3	_	_	-0.3	V	$I_{\rm C} = -1 \text{ A}, I_{\rm B} = -0.1 \text{ A}$
Gain bandwidth product	f <sub>T</sub>	_	150	_	_	150	_	MHz	$V_{CE} = -2 \text{ V}, I_{C} = -10 \text{ mA}$
Collector output capacitance	Cob	_	50	_	_	50	_	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz

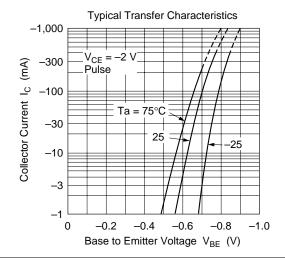
Note: 1. The 2SB738 and 2SB739 are grouped by  $h_{\text{FE}}$  as follows.

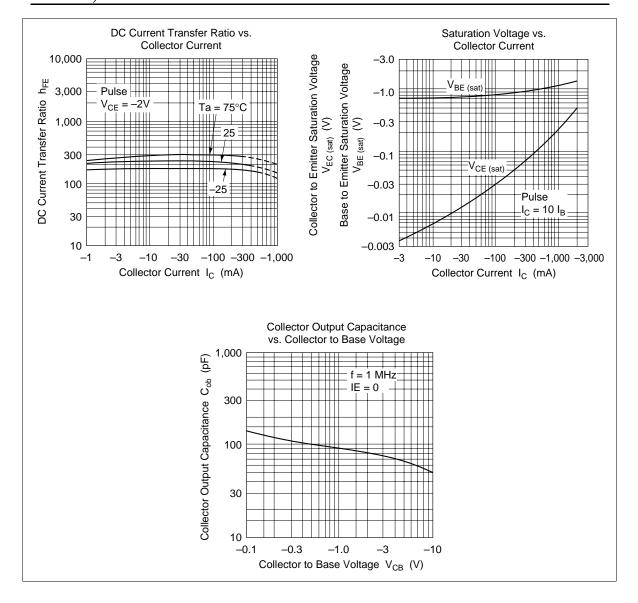
B C 100 to 200 160 to 320



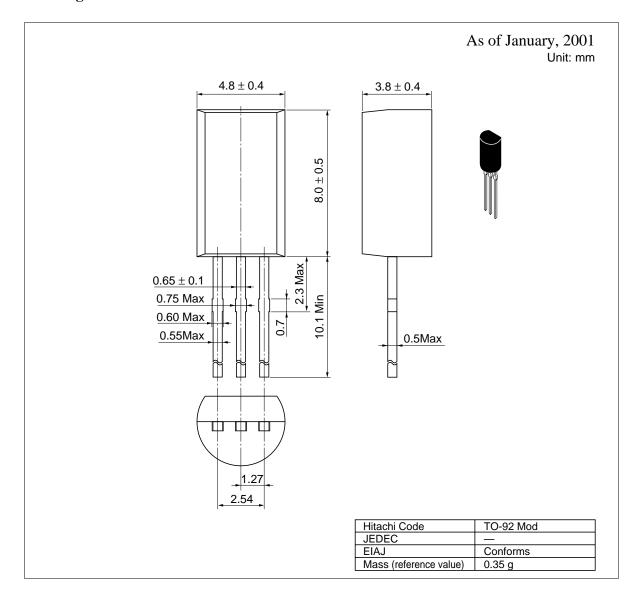








#### **Package Dimensions**



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